

ABSTRACT OF THE DISCLOSURE

Disclosed is a high power semiconductor laser device having a low far-field vertical angle (FFV) and excellent optical power efficiency. The semiconductor laser device comprises a semiconductor substrate, a lower clad layer formed on the semiconductor substrate, a lower guide layer formed on the lower clad layer, an active layer formed on the lower guide layer, an upper guide layer formed on the active layer, and an upper clad layer formed on the upper guide layer, wherein the lower and upper clad layers have the same refractivity, and the lower clad layer includes a high refractivity layer, spaced from the lower guide layer by a constant distance, with refractivity higher than that of the upper clad layer.